Supplemental information

References

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Plots

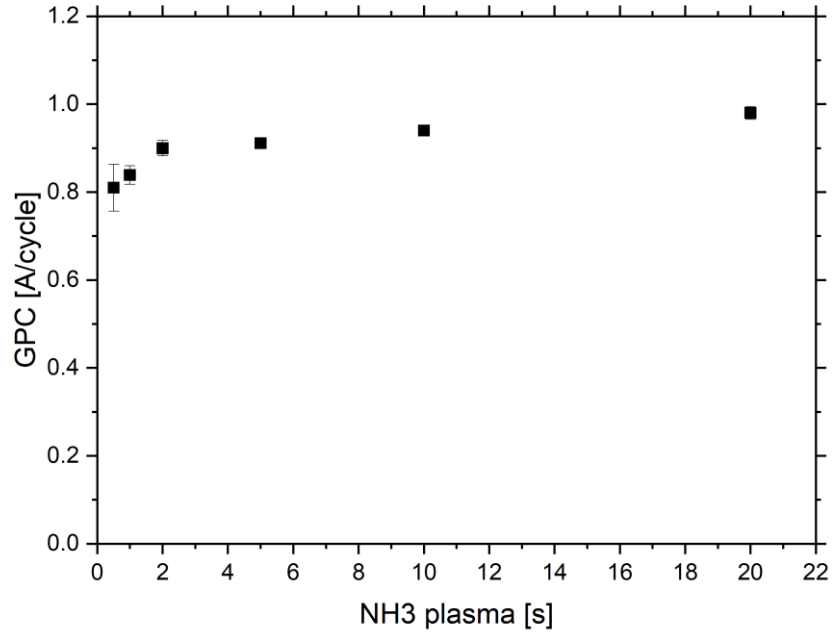

Figure 1: Growth per cycle as a function of NH3 plasma duration for AlN films grown at 200 °C. GPC values represent average and 1σ standard deviations of 49 points on 200 mm wafers with 10 mm edge exclusion.

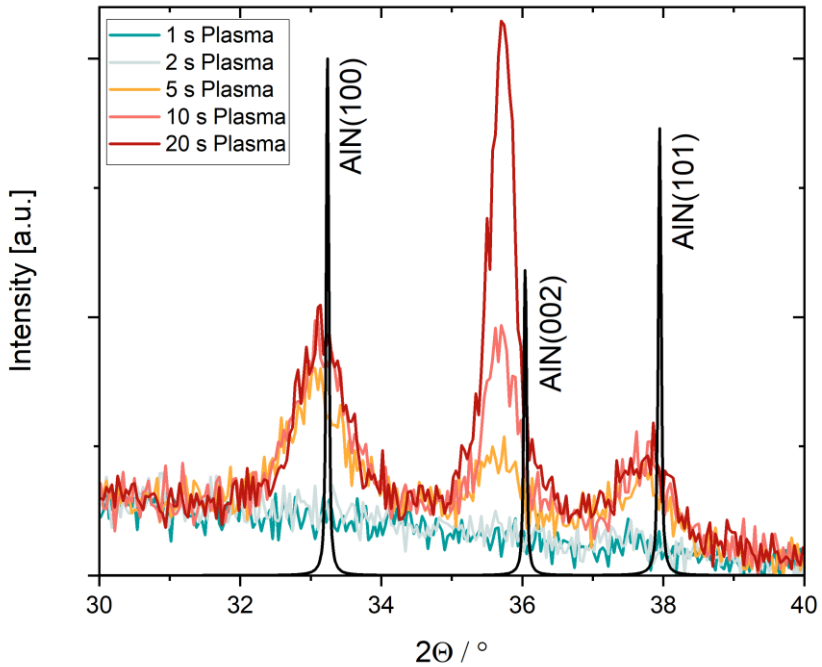

Figure 2: Grazing-incidence X-ray diffraction patterns of ~55 nm AlN thin films grown at 200 °C with varying NH3 plasma durations. Black patterns show reference data (COD ID 9011657).